

ABSTRACT

It is an object of the present invention to effectively manufacture a charged-particle beam lithography mask, an X-ray lithography mask, or an extreme ultraviolet beam lithography mask by using, for example, an existing writer such as an electron beam writer for photomasks, while achieving improvement in processing accuracy of a mask pattern. A lithography mask (1) comprises a substrate (2) which has a lower surface provided substantially at the center thereof with an opening (3) and a self-supporting membrane (m) having a pattern region (4) substantially at the center of an upper surface of the substrate (2) corresponding to the opening (3). The self-supporting membrane (m) is provided with through-holes (h) of a mask pattern in it or an absorber or scatterer of a mask pattern on it, and the pattern region (4) and a peripheral region around the pattern region (5) are in one plane.